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Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

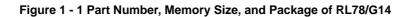
#### Details

Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	82
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	8K x 8
RAM Size	12K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 20x8/10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104pfdfb-v0

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

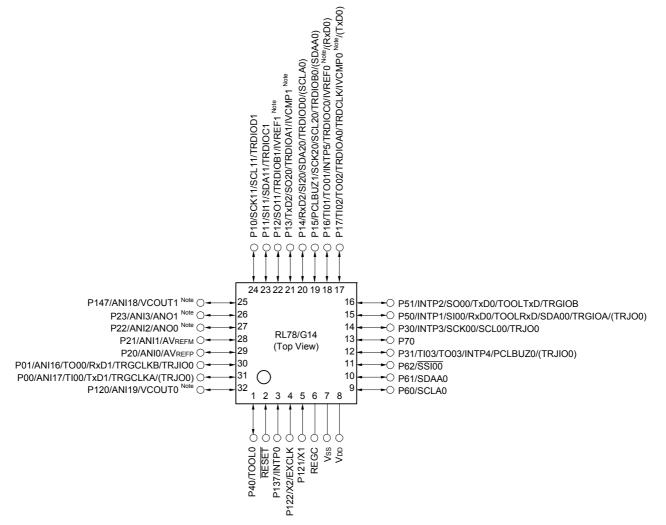
# 1.2 Ordering Information



Part No. R5F104LEAxxxFB#V0 Packaging specification #30: Tray (LFQFP, LQFP) #U0: Tray (HWQFN, WFLGA, FLGA) #V0: Tray (LFQFP, LQFP, LSSOP) #50: Embossed Tape (LFQFP, LQFP) #W0:Embossed Tape (HWQFN, WFLGA, FLGA) #X0: Embossed Tape (LFQFP, LQFP, LSSOP) Package type: SP: LSSOP, 0.65 mm pitch FP: LQFP, 0.80 mm pitch FA: LQFP, 0.65 mm pitch FB: LFQFP, 0.50 mm pitch NA: HWQFN, 0.50 mm pitch LA: WFLGA, 0.50 mm pitch FLGA, 0.50 mm pitch ROM number (Omitted with blank products) Fields of application: A: Consumer applications, TA = -40 to +85 °C D: Industrial applications, TA = -40 to +85  $^{\circ}$ C G: Industrial applications, TA = -40 to +105 °C ROM capacity: A: 16 KB C: 32 KB D: 48 KB E: 64 KB F: 96 KB G: 128 KB H: 192 KB J: 256 KB K: 384 KB L: 512 KB Pin count: A: 30-pin B: 32-pin C: 36-pin E: 40-pin F: 44-pin G: 48-pin J: 52-pin L: 64-pin M: 80-pin P: 100-pin RL78/G14 Memory type: F : Flash memory Renesas MCU Renesas semiconductor product



• 32-pin plastic LQFP (7 × 7 mm, 0.8 mm pitch)

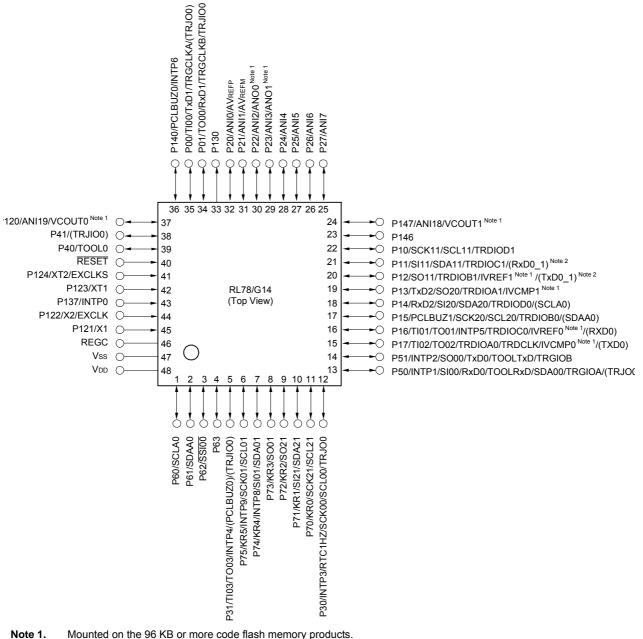


- Note Mounted on the 96 KB or more code flash memory products.
- Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).

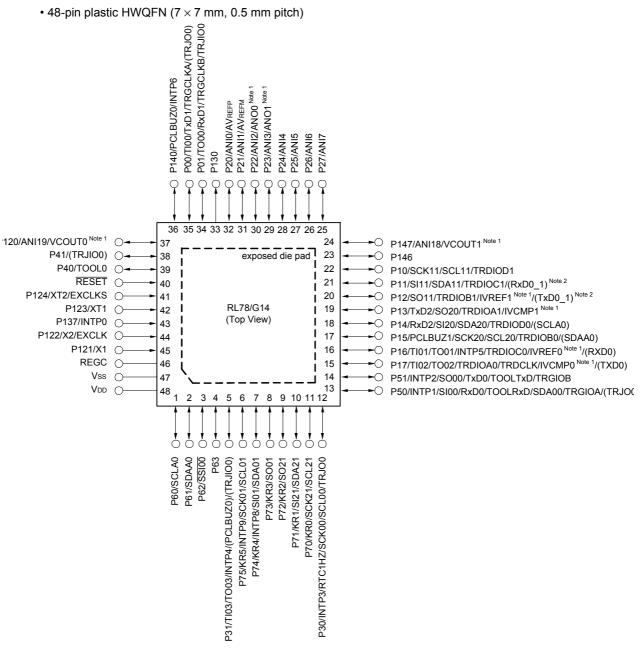


## 1.3.6 48-pin products

• 48-pin plastic LFQFP (7 × 7 mm, 0.5 mm pitch)



- Note 2. Mounted on the 384 KB or more code flash memory products.
- Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).



**Note 1.** Mounted on the 96 KB or more code flash memory products.

Note 2. Mounted on the 384 KB or more code flash memory products.

- Caution Connect the REGC pin to Vss pin via a capacitor (0.47 to 1  $\mu$ F).
- Remark 1. For pin identification, see 1.4 Pin Identification.
- **Remark 2.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register 0, 1 (PIOR0, 1).
- Remark 3. It is recommended to connect an exposed die pad to Vss.



[44-pin, 48-pin, 52-pin, 64-pin products (code flash memory 16 KB to 64 KB)]

# Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

					(1/2			
		44-pin	48-pin	52-pin	64-pin			
	Item	R5F104Fx	R5F104Gx	R5F104Jx	R5F104Lx			
		(x = A, C to E)	(x = A, C to E)	(x = C  to  E)	(x = C to E)			
Code flash me	emory (KB)	16 to 64	16 to 64	32 to 64	32 to 64			
Data flash me	mory (KB)	4	4	4	4			
RAM (KB)		2.5 to 5.5 Note	2.5 to 5.5 Note	4 to 5.5 Note	4 to 5.5 Note			
Address spac	e	1 MB						
Main system clock	High-speed system clock	HS (high-speed main) HS (high-speed main) LS (low-speed main) n	cillation, external main s mode: 1 to 20 MHz (Vr mode: 1 to 16 MHz (Vr node: 1 to 8 MHz (Vr mode: 1 to 4 MHz (Vr	D = 2.7  to  5.5  V), D = 2.4  to  5.5  V), D = 1.8  to  5.5  V),	ICLK)			
	High-speed on-chip oscillator clock (fiH)	HS (high-speed main) LS (low-speed main) n	mode:1 to 32 MHz (Vcmode:1 to 16 MHz (Vcnode:1 to 8 MHz (Vcmode:1 to 4 MHz (Vc	DD = 2.4 to 5.5 V), D = 1.8 to 5.5 V),				
Subsystem cl	ock	XT1 (crystal) oscillation	n, external subsystem cl	ock input (EXCLKS) 3	2.768 kHz			
Low-speed or	n-chip oscillator clock	15 kHz (TYP.): Vod = 1	.6 to 5.5 V					
General-purpo	ose register	8 bits $\times$ 32 registers (8 bits $\times$ 8 registers $\times$ 4 banks)						
Minimum instr	ruction execution time	0.03125 μs (High-speed on-chip oscillator clock: fiн = 32 MHz operation)						
		0.05 μs (High-speed system clock: f <sub>MX</sub> = 20 MHz operation)						
		30.5 µs (Subsystem clock: fsub = 32.768 kHz operation)						
Instruction set	ſ	<ul> <li>Multiplication (8 bits &gt;</li> <li>Multiplication and Activation</li> </ul>	/logical operation (8/16 < 8 bits, 16 bits × 16 bits cumulation (16 bits × 16 nd bit manipulation (Set	), Division (16 bits ÷ 16 bits + 32 bits)				
I/O port	Total	40	44	48	58			
	CMOS I/O	31	34	38	48			
	CMOS I/O CMOS input	31 5	34 5	38 5	48			
		_	-		_			
	CMOS input	_	5	5	5			
Гimer	CMOS input CMOS output N-ch open-drain I/O	5 — 4 8 channels	5	5 1 4	5 1 4			
Гimer	CMOS input CMOS output N-ch open-drain I/O (6 V tolerance)	5 — 4 8 channels	5 1 4	5 1 4	5 1 4			
Timer	CMOS input CMOS output N-ch open-drain I/O (6 V tolerance) 16-bit timer	5 — 4 8 channels (TAU: 4 channels, Time	5 1 4	5 1 4	5 1 4			
Timer	CMOS input CMOS output N-ch open-drain I/O (6 V tolerance) 16-bit timer Watchdog timer Real-time clock	5 — 4 8 channels (TAU: 4 channels, Time 1 channel	5 1 4	5 1 4	5 1 4			
Timer	CMOS input CMOS output N-ch open-drain I/O (6 V tolerance) 16-bit timer Watchdog timer Real-time clock (RTC)	5 — 4 8 channels (TAU: 4 channels, Time 1 channel 1 channel	5 1 4 er RJ: 1 channel, Timer	5 1 4	5 1 4			

(Note is listed on the next page.)

RENESAS

- Note 1. Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVss0, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
   Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}_{\text{@1}} \text{ MHz to } 32 \text{ MHz}$ 

2.4 V  $\leq$  VDD  $\leq$  5.5 V@1 MHz to 16 MHz

LS (low-speed main) mode:  $$1.8~V \le V \mbox{DD} \le 5.5~V \ensuremath{\textcircled{@}1}$  MHz to 8 MHz

LV (low-voltage main) mode:  $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$  to 4 MHz

- Remark 1. fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- **Remark 3.** fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsuB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



# 2.4 AC Characteristics

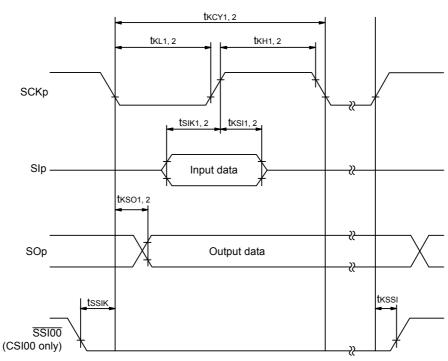
Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min-	Тсү	Main system	HS (high-speed main)	$2.7~V \leq V \text{DD} \leq 5.5~V$	0.03125		1	μs
imum instruction exe-		clock (fmain)	mode	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	0.0625		1	μs
cution time)		operation	LS (low-speed main) mode	$1.8 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$	0.125		1	μs
			LV (low-voltage main) mode	$1.6 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$	0.25		1	μs
		Subsystem clo	ock (fsuв) operation	$1.8~V \le V_{DD} \le 5.5~V$	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7~V \leq V \text{DD} \leq 5.5~V$	0.03125		1	μs
		program-	mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μs
		ming mode	LS (low-speed main) mode	$1.8 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$	0.125		1	μs
			LV (low-voltage main) mode	$1.8 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$	0.25		1	μs
External system clock	fEX	$2.7 \text{ V} \leq \text{Vdd} \leq 5.5 \text{ V}$			1.0		20.0	MHz
frequency		$2.4~V \leq V_{DD} \leq$	2.7 V		1.0		16.0	MHz
		$1.8 \text{ V} \leq \text{V}_{DD} <$	2.4 V		1.0		8.0	MHz
		$1.6 V \le V_{DD} <$	1.8 V		1.0		4.0	MHz
	fexs				32		35	kHz
External system clock	texн,	$2.7 \text{ V} \leq \text{V}\text{DD} \leq 5.5 \text{ V}$			24			ns
input high-level width,	tEXL	$2.4~V \leq V_{DD} \leq$	2.7 V		30			ns
low-level width		$1.8 \text{ V} \leq \text{V}_{DD} <$	2.4 V		60			ns
		$1.6 \text{ V} \leq \text{V}_{DD} <$	1.8 V		120			ns
	texhs, texls				13.7			μs
TI00 to TI03, TI10 to TI13 input high-level width, low-level width	ttiH, tti∟				1/fмск + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	100			ns
				$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$	300			ns
				$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V}$	500			ns
Timer RJ input high-	tтjiн,	TRJIO		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	40			ns
level width, low-level	t⊤ji∟			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$	120			ns
width				1.6 V ≤ EVDD0 < 1.8 V	200			ns

#### (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

NoteThe following conditions are required for low voltage interface when EVDD0 < VDD $1.8 V \le EVDD0 < 2.7 V$ : MIN. 125 ns $1.6 V \le EVDD0 < 1.8 V$ : MIN. 250 ns

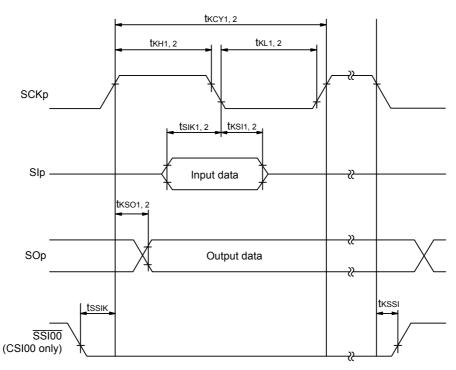
Remark fMCK: Timer array unit operation clock frequency (Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3))





# CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31) Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

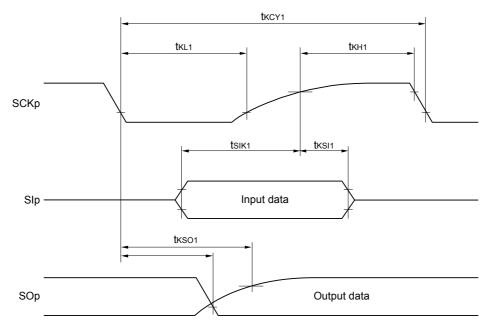
Parameter	Symbol	Conditions		speed main) ode		peed main) ode	•	oltage main) iode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{array}{l} 2.7 \ \text{V} \leq EV_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$		1000 Note 1		400 Note 1		400 Note 1	kHz
		$\label{eq:loss} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 3  k\Omega \end{array}$		400 Note 1		400 Note 1		400 Note 1	kHz
		$\label{eq:loss} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$		300 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:bound} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$		250 Note 1		250 Note 1		250 Note 1	kHz
		$\label{eq:bound} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$		-		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	t∟ow	$\begin{array}{l} 2.7 \ \text{V} \leq EV_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	475		1150		1150		ns
		$\label{eq:loss} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} \leq 5.5 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 3  k\Omega \end{array}$	1150		1150		1150		ns
		$\label{eq:bound} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$	1550		1550		1550		ns
		$\label{eq:bound} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$	1850		1850		1850		ns
		$\label{eq:bound} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$	—		1850		1850		ns
Hold time when SCLr = "H"	tніgн	$\begin{array}{l} 2.7 \ \text{V} \leq EV_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	475		1150		1150		ns
		$\begin{array}{l} 1.8 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 3 \text{ k}\Omega \end{array}$	1150		1150		1150		ns
		$\label{eq:bound} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_{\mbox{b}} \mbox{=} 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} \mbox{=} 5 \mbox{ k}\Omega \end{array}$	1550		1550		1550		ns
		$\label{eq:bound} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$	1850		1850		1850		ns
		$\label{eq:loss} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$	_		1850		1850		ns

#### (5) During communication at same potential (simplified I<sup>2</sup>C mode)

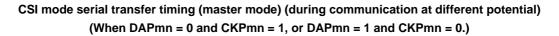
#### (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

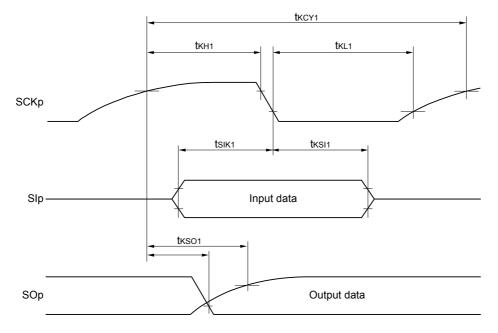
(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)





CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)





- Remark 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin: ANI0, ANI2 to ANI14, ANI16 to ANI20

(TA = -40 to +85°C, 2.4 V  $\leq$  VDD  $\leq$  5.5 V, 1.6 V  $\leq$  EVDD = EVDD1  $\leq$  VDD, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VBGR <sup>Note 3</sup>, Reference voltage (-) = AVREFM = 0 V <sup>Note 4</sup>, HS (high-speed main) mode)

Parameter	Symbol	Co	Conditions		TYP.	MAX.	Unit
Resolution	RES				8		bit
Conversion time	tCONV	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	% FSR
Integral linearity error Note 1	ILE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±1.0	LSB
Analog input voltage	VAIN		·	0		VBGR Note 3	V

**Note 1.** Excludes quantization error (±1/2 LSB).

Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 2.6.2 Temperature sensor characteristics/internal reference voltage characteristic.

Note 4. When reference voltage (-) = Vss, the MAX. values are as follows.

Zero-scale error:Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.Integral linearity error:Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.Differential linearity error:Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.



#### **Absolute Maximum Ratings**

(2/2)

					(214
Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Юн1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	-40	mA
		Total of all pins	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	-70	mA
		-170 mA	P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	-100	mA
	Іон2	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	IOL1	Per pin	P00 to P06, P10 to P17, P30, P31, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P100 to P102, P110, P111, P120, P130, P140 to P147	40	mA
		Total of all pins	P00 to P04, P40 to P47, P102, P120, P130, P140 to P145	70	mA
		170 mA	P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P100, P101, P110, P111, P146, P147	100	mA
	IOL2	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient temperature	Та		pperation mode	-40 to +105	°C
Storage temperature	Tstg			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



# 3.2 Oscillator Characteristics

# 3.2.1 X1, XT1 characteristics

#### $(TA = -40 \text{ to } +105^{\circ}C, 2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Resonator	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) Note	Ceramic resonator/	$2.7~V \leq V \text{DD} \leq 5.5~V$	1.0		20.0	MHz
	crystal resonator	$2.4 \text{ V} \le \text{V}_{\text{DD}} \le 2.7 \text{ V}$	1.0		16.0	
XT1 clock oscillation frequency (fxT) Note	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator in the RL78/G14 User's Manual.

# 3.2.2 On-chip oscillator characteristics

#### (TA = -40 to +105°C, 2.4 V $\leq$ VDD $\leq$ 5.5 V, Vss = 0 V)

Oscillators	Parameters	Conditions		MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator clock frequency		-20 to +85°C	$2.4~V \leq V \text{DD} \leq 5.5~V$	-1.0		+1.0	%
accuracy		-40 to -20°C	$2.4~V \leq V \text{DD} \leq 5.5~V$	-1.5		+1.5	%
		+85 to +105°C	$2.4~V \leq V \text{DD} \leq 5.5~V$	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Note 1. High-speed on-chip oscillator frequency is selected with bits 0 to 4 of the option byte (000C2H) and bits 0 to 2 of the HOCODIV register.

Note 2. This only indicates the oscillator characteristics. Refer to AC Characteristics for instruction execution time.



#### Parameter Symbo Conditions MIN. TYP. MAX. fносо = 64 MHz, $V_{DD} = 5.0 V$ 2.6 Supply DD1 Operat-HS (high-speed main) Basic current ing mode mode Note 5 fill = 32 MHz Note 3 operation VDD = 3.0 V 2.6 Note 1 fносо = 32 MHz. Basic VDD = 5.0 V 2.3 fiH = 32 MHz Note 3 operation VDD = 3.0 V 2.3 fносо = 64 MHz, VDD = 5.0 V HS (high-speed main) Normal 5.4 10.9 mode Note 5 fiH = 32 MHz Note 3 operation $V_{DD} = 3.0 V$ 54 10.9 VDD = 5.0 V 10.3 fносо = 32 MHz. Normal 5.0 fin = 32 MHz Note 3 operation VDD = 3.0 V 10.3 5.0 VDD = 5.0 V fHOCO = 48 MHz. 42 82 Normal fiH = 24 MHz Note 3 operation VDD = 3.0 V 4.2 8.2 fносо = 24 MHz, Normal VDD = 5.0 V 4.0 7.8 fill = 24 MHz Note 3 operation VDD = 3.0 V 40 78 fносо = 16 MHz, Normal VDD = 5.0 V 3.0 5.6 fin = 16 MHz Note 3 operation VDD = 3.0 V 3.0 5.6 HS (high-speed main) 3.4 f<sub>MX</sub> = 20 MHz Note 2 Normal Square wave input 6.6 mode Note 5 VDD = 5.0 V operation Resonator connection 3.6 6.7 f<sub>MX</sub> = 20 MHz Note 2, Normal Square wave input 34 6.6 operation $V_{DD} = 3.0 V$ Resonator connection 3.6 6.7 fmx = 10 MHz Note 2, 2.1 3.9 Normal Square wave input VDD = 5.0 V operation Resonator connection 22 4.0 f<sub>MX</sub> = 10 MHz Note 2. Normal Square wave input 2.1 3.9 VDD = 3.0 V operation Resonator connection 2.2 4.0 fsub = 32.768 kHz Note 4 49 71 Subsystem clock Normal Square wave input operation operation $T_A = -40^{\circ}C$ Resonator connection 4.9 7.1 fsub = 32.768 kHz Note 4 Normal Square wave input 4.9 7.1 $T_A = +25^{\circ}C$ operation 4.9 7.1 Resonator connection Normal 5.1 8.8 fsub = 32.768 kHz Note 4 Square wave input $T_A = +50^{\circ}C$ operation 8.8 Resonator connection 5.1 10.5 fsub = 32.768 kHz Note 4 Square wave input 5.5 Normal TA = +70°C operation Resonator connection 5.5 10.5 fsub = 32.768 kHz Note 4 Normal 6.5 14.5 Square wave input TA = +85°C operation 6.5 14.5 Resonator connection fsub = 32.768 kHz Note 4 Normal Square wave input 13.0 58.0

 $T_{A} = +105^{\circ}C$ 

## (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

#### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(Notes and Remarks are listed on the next page.)

operation

Resonator connection

Unit

mΑ

mΑ

mΑ

μA

13.0

58.0

#### RL78/G14

- Note 1. Total current flowing into VDD, EVDD0, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0, and EVDD1, or Vss, EVss0, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, D/A converter, comparator, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.

Note 5.Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.<br/>HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$  to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$  to 16 MHz

Remark 1. fMX: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)

- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fill: High-speed on-chip oscillator clock frequency (32 MHz max.)
- Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



# 3.4 AC Characteristics

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (min- imum instruction exe- cution time)	Тсү	Main system	HS (high-speed main)	$2.7~V \leq V_{DD} \leq 5.5~V$	0.03125		1	μs
		clock (fmAIN) mode operation	mode	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
		Subsystem clo	ock (fsuв) operation	$2.4~V \le V_{DD} \le 5.5~V$	28.5	30.5	31.3	μs
		In the self-	HS (high-speed main)	$2.7~V \leq V_{DD} \leq 5.5~V$	0.03125		1	μs
		program- ming mode	mode	$2.4 \text{ V} \leq \text{V}_{\text{DD}} < 2.7 \text{ V}$	0.0625		1	μs
External system clock	fEX	$2.7~V \leq V \text{DD} \leq$	5.5 V		1.0		20.0	MHz
frequency		$2.4~V \leq V \text{DD} \leq$	2.7 V		1.0		16.0	MHz
	fexs				32		35	kHz
External system clock	texн,	$2.7~V \leq V \text{DD} \leq$	5.5 V		24			ns
input high-level width,	<b>t</b> EXL	$2.4~V \leq V \text{DD} \leq$	2.7 V		30			ns
low-level width	texhs, texls				13.7			μs
TI00 to TI03, TI10 to TI13 input high-level width, low-level width	t⊤ıн, t⊤ı∟				1/fмск + 10 Note			ns
Timer RJ input cycle	fc	TRJIO		$2.7 \text{ V} \leq EV \text{DD0} \leq 5.5 \text{ V}$	100			ns
				$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V}$	300			ns
Timer RJ input high-	tтjiн,	TRJIO		$2.7 \text{ V} \leq EV \text{DD0} \leq 5.5 \text{ V}$	40			ns
level width, low-level width	t⊤ji∟			$2.4 \text{ V} \le \text{EVdd0} < 2.7 \text{ V}$	120			ns

#### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

NoteThe following conditions are required for low voltage interface when EVDD0 < VDD2.4 V  $\leq EVDD0 < 2.7$  V: MIN. 125 ns

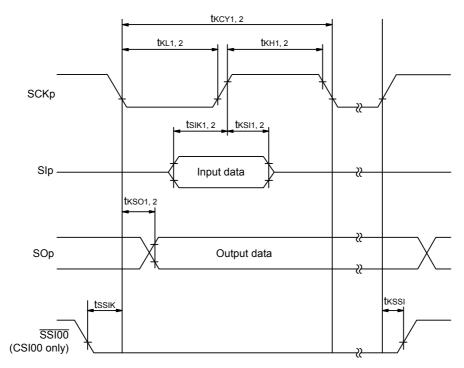
RemarkfMCK: Timer array unit operation clock frequency<br/>(Operation clock to be set by the CKSmn bit of timer mode register mn (TMRmn). m: Unit number (m = 0, 1), n: Channel<br/>number (n = 0 to 3))



# Interrupt Request Input Timing INTPO to INTP11 Key Interrupt Input Timing KR0 to KR7 RESET Input Timing

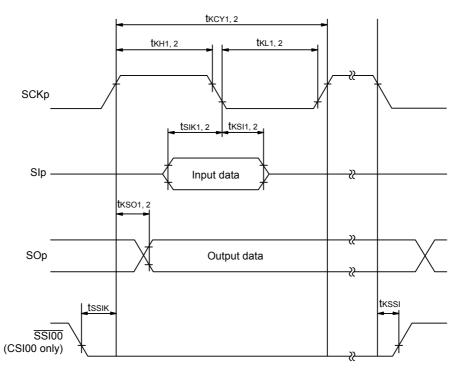
RESET





#### CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)

CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



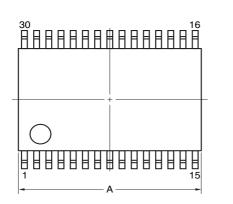
Remark 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31) Remark 2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

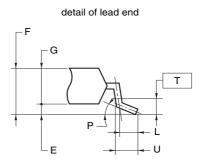
# 4. PACKAGE DRAWINGS

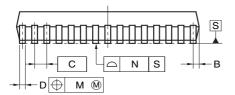
# 4.1 30-pin products

R5F104AAASP, R5F104ACASP, R5F104ADASP, R5F104AEASP, R5F104AFASP, R5F104AGASP R5F104AADSP, R5F104ACDSP, R5F104ADDSP, R5F104AEDSP, R5F104AFDSP, R5F104AGDSP R5F104AAGSP, R5F104ACGSP, R5F104ADGSP, R5F104AEGSP, R5F104AFGSP, R5F104AGGSP

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

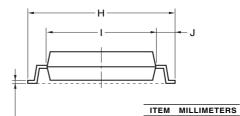






#### NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.



·κ

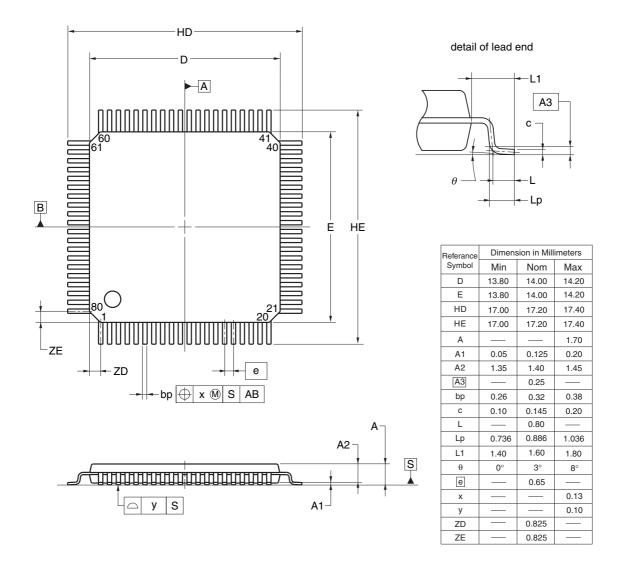
A 9.85±0.15 в 0.45 MAX С 0.65 (T.P.)  $0.24_{-0.07}^{+0.08}$ D F 0.1±0.05 F 1.3±0.1 G 1.2 8.1±0.2 Н 6.1±0.2 I 1.0±0.2 J 0.17±0.03 κ L 0.5 0.13 Μ Ν 0.10 Р 3°+5° 0.25 т 0.6±0.15 U

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R5F104MFAFA, R5F104MGAFA, R5F104MHAFA, R5F104MJAFA R5F104MFDFA, R5F104MGDFA, R5F104MHDFA, R5F104MJDFA R5F104MFGFA, R5F104MGGFA, R5F104MHGFA, R5F104MJGFA R5F104MKAFA, R5F104MLAFA R5F104MKGFA, R5F104MLGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69



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